PCN Number:	20240605000.2	PCN Date:	June 05, 2024
Title:	Add Cu as Alternative Wire Base Metal for Selected Device(s)		
Customer Contact:	Change Management team	Dept:	Quality Services
Proposed 1st Ship Date:	December 02, 2024	Sample requests accepted until:	July 05, 2024

***Sample requests received after** July 05, 2024 **will not be supported.**

Change Type:

☐	Assembly Site	☐	Design	☐	Wafer Bump Material
☒	Assembly Process	☐	Data Sheet	☐	Wafer Bump Process
☒	Assembly Materials	☐	Part number change	☐	Wafer Fab Site
☐	Mechanical Specification	☐	Test Site	☐	Wafer Fab Material
☐	Packing/Shipping/Labeling	☐	Test Process	☐	Wafer Fab Process

PCN Details

Description of Change:

Texas Instruments is pleased to announce the qualification of new assembly material set to add Cu as an additional bond wire option for devices listed in "Product affected" section below. Devices will remain in current assembly facility and piece part changes as follows:

Material	Current*	Proposed
Wire type	0.96mil Au, 1.0mil Cu	0.8mil Cu

Note: * - Au wire: Die to die bonding, Cu wire: Die to leadframe

Reason for Change:

Continuity of supply.

1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties
2) Maximize flexibility within our Assembly/Test production sites.
3) Cu is easier to obtain and stock

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☒ No Change	☒ No Change	☒ No Change	☒ No Change

Changes to product identification resulting from this PCN:

None

Product Affected:

ISO1540QDRQ1	ISO1640BQDRQ1	ISO6720FBQDRQ1	ISO6721FBQDRQ1
ISO1541QDRQ1	ISO6720BQDRQ1	ISO6721BQDRQ1	UCC5350SBQDRQ1

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)
Approve Date 01-May-2024

Product Attributes

Attributes	Qual Device: ISO6721RBQDRQ1	QBS Package Reference: ISO6721BQDRQ1	QBS Package Reference: TLV9022QDRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Product Reference: ISO1640QDWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Signal Chain	Power Management	Interface
Wafer Fab Supplier	RFAB, RFAB	MH8, MH8	RFAB	RFAB, RFAB	RFAB, RFAB
Assembly Site	MLA	MLA	MLA	TAI	MLA
Package Group	SOIC	SOIC	-	SOIC	SOIC
Package Designator	D	D	D	DWY	DW
Pin Count	8	8	8	6	16

QBS: Qual By Similarity
Qual Device ISO6721RBQDRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6721RBQDRQ1	QBS Package Reference: ISO6721BQDRQ1	QBS Package Reference: TLV9022QDRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Product Reference: ISO1640QDWRQ1
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	-	No Fails	No Fails	-	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	-	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	3/231/0	-	-
TC-SAM	A4	-	3	3	Post TC SAM	<50% delamination	-	-	1/12/0	-	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	3/135/0	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	3/135/0	-	-	-
Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	3/231/0	3/231/0	3/231/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	-	3/2400/0	-
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/228/0	3/90/0	-	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/228/0	3/90/0	-	1/30/0

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6721RBQDRQ1	QBS Package Reference: ISO6721BQDRQ1	QBS Package Reference: TLV9022QDRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Product Reference: ISO1640QDWRQ1
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	3/30/0	-	-
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/3/0	1/6/0	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	3/90/0	3/90/0	3/90/0	1/30/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)
Approve Date 05-April-2024

Product Attributes

Attributes	Qual Device: UCC5350MCQDRQ1	Qual Device: UCC5350MCQDRQ1	QBS Package Reference: ISO6721BQDRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: AMC22C12QDRQ1	QBS Product Reference: UCC5390ECQDWVQ1	QBS Product Reference: UCC5350MCQDRQ1	QBS Package Reference: UCC21520QDWRQ1	QBS Package Reference: ISO5452QDWR	QBS Package, Process, Product Reference: UCC5350SBQDRQ1	QBS Package Reference: UCC21540QDWKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Signal Chain	Signal Chain	Interface	Power Management	Signal Chain	Interface	Interface	Power Management	Power Management	Signal Chain	Power Management
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	MH8, MH8	RFAB, RFAB	MH8, DMOS6	DP1DM5, DP1DM5	DP1DM5, DP1DM5	DP1DM5, DP1DM5, DP1DM5	DP1DM5, DP1DM5, MH8	RFAB, RFAB	MH8, MH8, MH8
Assembly Site	TAI	MLA	MLA	TAI	MLA	TAI	TAI	TAI	MLA	MLA	TAI
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	D	D	D	DWY	D	DWV	D	DW	DW	D	DWK
Pin Count	8	8	8	6	8	8	8	16	16	8	14

QBS: Qual By Similarity
Qual Device UCC5350MCQDRQ1 is qualified at MSL2 260C
Qual Device UCC5350MCQDRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: UCC5350MCQDRQ1	Qual Device: UCC5350MCQDRQ1	QBS Package Reference: ISO6721BQDRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: AMC22C12QDRQ1	QBS Product Reference: UCC5390ECQDWVQ1	QBS Product Reference: UCC5350MCQDRQ1	QBS Package Reference: UCC21520QDWRQ1	QBS Package Reference: ISO5452QDWR	QBS Package, Process, Product Reference: UCC5350SBQDRQ1	QBS Package Reference: UCC21540QDWKRQ1
Test Group A - Accelerated Environment Stress Tests																		
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	-	-	3/0/0	-	-	-	-	-	-	-	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	1/0/0	-	-	3/0/0	-	-	3/0/0	1/0/0	-	1/0/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	-	-	-	-	-	-	1/77/0	-	2/154/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	3/231/0	-	-	-	-	-	1/77/0	-	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	-	-	3/231/0	-	-	-	-	-	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	-	-	-	-	1/77/0	-	-	2/154/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	-	-	-	-	-	-	-	1/5/0	-	-	-
TC-SAM	A4	-	3	3	Post TC SAM	<50% delamination	-	-	-	1/12/0	-	-	-	-	-	-	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	-	3/135/0	-	-	-	1/45/0	-	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	3/135/0	-	-	-	-	-	-	-	-
Test Group B - Accelerated Lifetime Simulation Tests																		
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	1/77/0	-	3/231/0	-	1/77/0	-	-	-	-	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	-	3/2400/0	-	-	-	-	-	-	-
Test Group C - Package Assembly Integrity Tests																		
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	3/228/0	-	3/90/0	-	-	-	-	1/30/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	3/228/0	-	3/90/0	-	-	-	-	1/30/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	1/15/0	-	-	-	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	1/15/0	-	-	-	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	1/10/0	3/30/0	-	3/30/0	-	-	-	-	1/10/0	-
Test Group D - Die Fabrication Reliability Tests																		
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests																		
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	-	-	-	-	-	1/3/0	1/3/0	-	-	1/3/0	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	-	-	-	-	-	1/3/0	1/3/0	-	-	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	-	-	-	-	-	1/6/0	-	-	-	1/6/0	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	-	-	-	-	-	1/30/0	1/30/0	-	-	1/30/0	-

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycle
Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)
Approve Date 19-October-2023

Product Attributes

Attributes	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Process Reference: ISO7741FQDWQ1	QBS Product Reference: ISO6763QDWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Power Management	Power Management	Interface	Interface
Wafer Fab Supplier	RFAB, RFAB	MH8, MH8, MH8	RFAB, RFAB	MH8, MH8	RFAB, RFAB
Assembly Site	MLA	TAI	TAI	TAI	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	DW	DWK	DWY	DW	DW
Pin Count	16	14	6	16	16

QBS: Qual By Similarity
Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C
Qual Device UCC21540QDWKRQ1 is qualified at MSL3 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Process Reference: ISO7741FQDWQ1	QBS Product Reference: ISO6763QDWRQ1
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	No Fails	No Fails	-	-	No Fails
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	3/231/0	-	-	1/77/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	3/231/0	3/231/0	-	-	1/77/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0	-	-	1/77/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	1/5/0	-	-	1/5/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	3/135/0	-	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	-	-	1/45/0

Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	-	3/231/0	3/231/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	3/2400/0	-
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0	3/90/0	-
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	1/15/0
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	-	-	3/30/0	-	-
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	Device specific data [1]	Device specific data [1]	-	-	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1500 Volts	Device specific data [1]	Device specific data [1]	-	-	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	Device specific data [1]	Device specific data [1]	-	-	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	3/90/0	3/90/0	3/90/0	-

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
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The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
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Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/
[1] Change from hybrid Au and Cu wires to full Cu wire in assembly will not impact HBM, CDM, and LU result.

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)
Approve Date 16-June-2023

Product Attributes

Attributes	Qual Device: UCC21520QDWRQ1	Qual Device: ISO5452DWR	QBS Reference: UCC21520QDWQ1	QBS Reference: ISO5851QDWQ1	QBS Reference: TMP451AQDQFRQ1	QBS Reference: AMC1305M25QDWQ1	QBS Reference: AMC1305M25QDWQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Power Management	Interface	Power Management	Signal Chain	Signal Chain
Wafer Fab Supplier	DP1DM5, DP1DM5, DP1DM5	DP1DM5, DP1DM5, MH8	DP1DM5, DP1DM5, DP1DM5	MH8, DP1DM5, DP1DM5	DP1DM5	DP1DM5, DP1DM5, AIZU	DP1DM5, DP1DM5, AIZU
Assembly Site	TAI	MLA	TAI	TAI	UTL1	MLA	TAI
Package Group	SOIC	SOIC	SOIC	SOIC	QFN	SOIC	SOIC
Package Designator	DW	DW	DW	DW	DQF	DW	DW
Pin Count	16	16	16	16	8	16	16

QBS: Qual By Similarity
Qual Device UCC21520QDWRQ1 is qualified at MSL2 260C
Qual Device ISO5452DWR is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: UCC21520QDWRQ1	Qual Device: ISO5452DWR	QBS Reference: UCC21520QDWQ1	QBS Reference: ISO5851QDWQ1	QBS Reference: TMP451AQDQFRQ1	QBS Reference: AMC1305M25QDWQ1	QBS Reference: AMC1305M25QDWQ1
Test Group A - Accelerated Environment Stress Tests														
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	-	-	-	-	No Fails	-	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	No Fails	No Fails	No Fails	No Fails	-	-	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	-	-	-	-	-	-	3/0/0	3/0/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	1/77/0	-	3/231/0	3/231/0	3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	1/77/0	1/77/0	1/77/0	3/231/0	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	1/77/0	1/77/0	1/77/0	3/231/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	1/5/0	-	-	1/5/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	1/45/0	-	-	-	3/135/0	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	-	1/45/0	1/45/0	-	-
Test Group B - Accelerated Lifetime Simulation Tests														
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	-	-	-	3/231/0	-	-	-
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	150C	408 Hours	-	-	-	-	3/231/0	-	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	-	3/2400/0	-	-	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	150C	24 Hours	-	-	-	-	3/2400/0	-	-
Test Group C - Package Assembly Integrity Tests														
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	-	1/30/0	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	-	1/30/0	3/90/0	3/90/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	-	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	-	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	-	-	1/10/0	3/30/0	-	-
Test Group D - Die Fabrication Reliability Tests														

EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests														
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	Device specific data [1]	Device specific data [1]	1/3/0	1/3/0	1/3/0	-	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	Device specific data [1]	Device specific data [1]	1/3/0	1/3/0	1/3/0	-	-
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	Device specific data [1]	Device specific data [1]	1/6/0	1/6/0	1/6/0	-	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	1/30/0	1/30/0	1/30/0	3/90/0	3/90/0	3/90/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/
TI Qualification ID: R-CHG-2203-108
[1] Qual Device: UCC21520QDWRQ1 and QBS Reference: UCC21520QDWQ1 use the same silicon die and bondout.
Qual Device: ISO5452DWR and QBS Reference: ISO5851QDWQ1 use the same silicon die and bondout.

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)
Approve Date 28-April-2023

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: AMC1305M25QDWQ1	Qual Device: AMC1305M25QDWQ1
Test Group A - Accelerated Environment Stress Tests									
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	1 Step	No Fails	No Fails
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	3/66/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	3/66/0	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-

HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	192 Hours	3/231/0	3/231/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	-
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-	-
TC	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	-	-
TC	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	-	-
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	3/3/0
TC	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
TC	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	-
HTSL	A6.2	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	2000 Hours	3/132/0	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	3/3/0

Test Group B - Accelerated Lifetime Simulation Tests									
Test Group C - Package Assembly Integrity Tests									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	-
Test Group D - Die Fabrication Reliability Tests									
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

QBS: Qual By Similarity
Qual Device AMC1305M25QDWQ1 is qualified at MSL3 260C
Qual Device AMC1305M25QDWQ1 is qualified at MSL3 260C
Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)
(Q100, Q006, Grade 1, -40/125C)
Approved 21-Dec-2023

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

	Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: UCC21330BQDRQ1	QBS Reference Device: TLV9022QDRQ1	QBS Reference Device: ISO6721BQDRQ1
Test Group A – Accelerated Environment Stress Tests										
	PC	A1	-	3	22	SAM Analysis, Pre Stress	Completed	3/66/0	3/66/0	-
	PC	**A1**	**JEDEC J-STD-020 JESD22-A113**	**3**	**77**	**Preconditioning**	**Level 2-260C**	**No fails**	**No fails**	**No fails**
	PC	A1	-	3	22	SAM Analysis, Post Stress	Completed	3/66/0	3/66/0	2/44/0
	HAST	**A2**	**JEDEC JESD22-A110**	**3**	**77**	**Biased HAST, 130C/85%RH**	**96 Hours**	-	**3/231/0**	**3/231/0**
	HAST	A2	-	3	1	Cross Section, Post bHAST 96 Hours	Completed	-	-	-
	HAST	A2	-	3	30	Wire Bond Shear, Post bHast 96 Hours	Wires	-	-	-
	HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	-	-	-
	HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	-	-	-
	HAST	**A2**	**JEDEC JESD22-A110**	**3**	**77**	**Biased HAST, 130C/85%RH**	**192 Hours**	-	**3/210/0**	**3/210/0**
	HAST	A2	-	3	1	Cross Section, Post bHAST 192 Hours	Completed	-	3/3/0	3/3/0
	HAST	A2	-	3	22	SAM Analysis, Post bHAST, 192 Hours	Completed	-	3/66/0	3/66/0
	HAST	A2	-	3	30	Wire Bond Shear, Post bHast 192 Hours	Wires	-	3/9/0	3/9/0
	HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	-	3/9/0	3/9/0
	HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	-	3/9/0	3/9/0
	TC	**A4**	**JEDEC JESD22-A104 and Appendix 3**	**3**	**77**	**Temperature Cycle, -65/150C**	**500 Cycles**	**3/231/0**	**3/231/0**	**3/231/0**
	TC	A4	-	3	1	Cross Section, Post T/C 500 Cycles	Completed	-	-	-
	TC	A4	-	3	22	SAM Analysis, Post T/C, 500 Cycles	Completed	-	-	-

	Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: UCC21330BQDRQ1	QBS Reference Device: TLV9022QDRQ1	QBS Reference Device: ISO6721BQDRQ1
	TC	A4	-	3	30	Wire Bond Shear, Post T/C 500 Cycles	Wires	-	-	-
	TC	A4	-	3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	-	-	-
	TC	A4	-	3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	-	-	-
	TC	**A4**	**JEDEC JESD22-A104 and Appendix 3**	**3**	**77**	**Temperature Cycle, -65/150C**	**1000 Cycles**	**3/210/0**	**3/210/0**	**3/210/0**
	TC	A4	-	3	1	Cross Section, Post T/C 1000 Cycles	Completed	3/3/0	3/3/0	3/3/0
	TC	A4	-	3	22	SAM Analysis, Post T/C, 1000 Cycles	Completed	3/66/0	3/66/0	3/66/0
	TC	A4	-	3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	3/9/0	3/9/0	3/9/0
	TC	A4	-	3	30	Bond Pull over Stitch, Post T/C, 1000 Cycles	Wires	3/9/0	3/9/0	3/9/0
	TC	A4	-	3	30	Bond Pull over Ball, Post T/C, 1000 Cycles	Wires	3/9/0	3/9/0	3/9/0
	PTC	**A5**	**JEDEC JESD22-A105**	**1**	**45**	**Power Temperature Cycle -40/125C**	**1000 Cycles**	**N/A**	**N/A**	**N/A**
	PTC	**A5**	**JEDEC JESD22-A105**	**1**	**45**	**Power Temperature Cycle -40/125C**	**2000 Cycles**	**N/A**	**N/A**	**N/A**
	HTSL	**A6**	**JEDEC JESD22-A103**	**3**	**45**	**High Temp Storage Bake 175C**	**500 Hours**	-	**3/231/0**	**3/135/0**
	HTSL	A6	-	3	1	Cross Section, Post HTSL 1000 Hours	Completed	-	-	-
	HTSL	**A6**	**JEDEC JESD22-A103**	**3**	**44**	**High Temp Storage Bake 150C**	**2000 Hours**	-	**3/210/0**	**3/132/0**
	HTSL	A6	-	3	1	Cross Section, Post HTSL 2000 Hours	Completed	-	3/3/0	3/3/0
Test Group C – Package Assembly Integrity Tests										
	WBS	C1	AEC Q100-001	3	30	Wire Bond Shear, Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0
	WBP	C2	MIL-STD883 Method 2011	3	30	Bond Pull over Ball, Cpk >1.67	Wires	3/90/0	3/90/0	3/90/0

- QBS: Qual By Similarity
- Qual Device UCC21330BQDRQ1 is qualified at LEVEL2-260C

A1 (PC): Preconditioning:
Performed for THB, Biased HAST, AC, uHAST & TC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Green/Pb-free Status:
Qualified Pb-Free(SMT) and Green

ZVEI ID: SEM-PA-08

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.